Product Preview

32K x 8 Bit Static Random Access Memory

The MCM6706CR is a 262,144 bit static random access memory organized as 32,768 words of 8 bits. Static design eliminates the need for external clocks or timing strobes. __

Output enable (G) is a special control feature that provides increased system flexibility and eliminates bus contention problems.

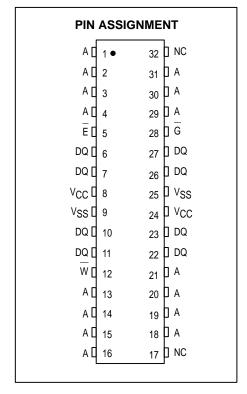
The MCM6706CR meets JEDEC standards and is available in a revolutionary pinout 300 mil, 32–lead surface–mount SOJ package.

- Single 5.0 V ± 10% Power Supply
- Fully Static No Clock or Timing Strobes Necessary
- All Inputs and Outputs Are TTL Compatible
- · Three State Outputs
- Fast Access Times: MCM6706CR-5 = 5 ns MCM6706CR-5.5 = 5.5 ns
- Center Power and I/O Pins for Reduced Noise

BLOCK DIAGRAM VCC Vss **MEMORY** ROW MATRIX DECODER 512 ROWS x 64 x 8 **COLUMNS** DQ0 COLUMN I/O **INPUT** COLUMN DECODER DATA CONTROL DO7

MCM6706CR





PIN NAMES					
A. Address W Write Enable E Chip Enable G Output Enable DQ Data Input/Output VCC + 5 V Power Supply VSS Ground NC No Connection					

This document contains information on a new product under development. Motorola reserves the right to change or discontinue this product without notice.

REV 1 10/9/96



TRUTH TABLE

E	G	w	Mode	I/O Pin	Cycle
Н	Х	Х	Not Selected	High–Z	_
L	Н	Н	Read	High–Z	_
L	L	Н	Read	D _{out}	Read Cycle
L	Х	L	Write	D _{in}	Write Cycle

ABSOLUTE MAXIMUM RATINGS (See Note)

Rating	Symbol	Value	Unit
Power Supply Voltage	Vcc	- 0.5 to + 7.0	V
Voltage Relative to V _{SS} for Any Pin Except V _{CC}	V _{in} , V _{out}	- 0.5 to V _{CC} + 0.5	V
Output Current	l _{out}	± 30	mA
Power Dissipation	PD	2.0	W
Temperature Under Bias	T _{bias}	- 10 to + 85	°C
Operating Temperature	T _A	0 to + 70	°C
Storage Temperature — Plastic	T _{stg}	- 55 to + 125	°C

NOTE: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPERATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high–impedance circuit.

This BiCMOS memory circuit has been designed to meet the dc and ac specifications shown in the tables, after thermal equilibrium has been established. The circuit is in a test socket or mounted on a printed circuit board and transverse air flow of at least 500 linear feet per minute is maintained.

DC OPERATING CONDITIONS AND CHARACTERISTICS

 $(V_{CC} = 5.0 \text{ V} \pm 10\%, T_A = 0 \text{ to } 70^{\circ}\text{C}, \text{ Unless Otherwise Noted})$

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Тур	Max	Unit
Supply Voltage (Operating Voltage Range)	Vcc	4.5	5.0	5.5	V
Input High Voltage	VIH	2.2	_	V _{CC} + 0.3*	V
Input Low Voltage	V _{IL}	- 0.5**	_	0.8	V

 $^{^*}$ V_{IH} (max) = V_{CC} + 0.3 V dc; V_{IH} (max) = V_{CC} + 2.0 V ac (pulse width \leq 2.0 ns) or I \leq 30.0 mA.

DC CHARACTERISTICS

Parameter	Symbol	Min	Max	Unit
Input Leakage Current (All Inputs, V _{in} = 0 to V _{CC})	llkg(l)	_	± 1.0	μΑ
Output Leakage Current (E = V _{IH} or G = V _{IH} , V _{out} = 0 to V _{CC})	l _{lkg(O)}	_	± 1.0	μΑ
Output High Voltage (I _{OH} = - 4.0 mA)	Voн	2.4	_	V
Output Low Voltage (I _{OL} = + 8.0 mA)	VoL	_	0.4	V

POWER SUPPLY CURRENTS

Parameter	Symbol	MCM6706CR-5	MCM6706CR-5.5	Unit	Notes
AC Active Supply Current $(I_{out} = 0 \text{ mA}, V_{CC} = \text{max}, f = f_{max})$	ICCA	240	235	mA	1, 2, 3
AC Standby Current (E = V_{IH} , V_{CC} = max, f = f_{max})	ISB1	120	115	mA	1, 2, 3
CMOS Standby Current ($V_{CC} = max$, $f = 0$ MHz, $E \ge V_{CC} - 0.2$ V, $V_{in} \le V_{SS}$, or $\ge V_{CC} - 0.2$ V)	ISB2	30	30	mA	

NOTES:

- 1. Reference AC Operating Conditions and Characteristics for input and timing (V_{IH}/V_{IL} , t_f/t_f , pulse level 0 to 3.0 V, V_{IH} = 3.0 V).
- 2. All addresses transition simultaneously low (LSB) and then high (MSB).
- 3. Data states are all zero.

^{**} V_{IL} (min) = -0.5 V dc @ 30.0 mA; V_{IL} (min) = -2.0 V ac (pulse width ≤ 2.0 ns) or $I \le 30.0$ mA.

CAPACITANCE (f = 1.0 MHz, dV = 3.0 V, T_A = 25°C, Periodically Sampled Rather Than 100% Tested)

Parameter	Symbol	Max	Unit
Address Input Capacitance	C _{in}	5	pF
Control Pin Input Capacitance (E, G, W)	C _{in}	6	pF
I/O Capacitance	C _{out}	6	pF

AC OPERATING CONDITIONS AND CHARACTERISTICS

 $(V_{CC} = 5.0 \text{ V} \pm 10\%, T_A = 0 \text{ to} + 70^{\circ}\text{C}, \text{ Unless Otherwise Noted})$

Input Timing Measurement Reference Level 1.5 V	Output Timing Measurement Reference Level 1.5 V
Input Pulse Levels 0 to 3.0 V	Output Load See Figure 1a
Input Rise/Fall Time	

READ CYCLE (See Notes 1 and 2)

		MCM6706CR-5		MCM6706CR-5.5			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Read Cycle Time	t _{AVAV}	5	_	5.5	_	ns	3
Address Access Time	†AVQV	_	5	_	5.5	ns	
Chip Enable Access Time	t _{ELQV}	_	5	_	5.5	ns	
Output Enable Access Time	t _{GLQV}	_	4	_	4	ns	
Output Hold from Address Change	tAXQX	2.0	_	2.0	_	ns	
Chip Enable Low to Output Active	t _{ELQX}	3	_	3	_	ns	4 ,5, 6
Chip Enable High to Output High–Z	t _{EHQZ}	_	3	_	3	ns	4, 5, 6
Output Enable Low to Output Active	t _{GLQX}	0	_	0	_	ns	4, 5, 6
Output Enable High to Output High–Z	^t GHQZ	_	3	_	3	ns	4, 5, 6

NOTES:

- 1. W is high for read cycle.
- 2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
- 3. All read cycle timing is referenced from the last valid address to the first transitioning address.
- 4. At any given voltage and temperature, tehQZ max < telQX min, and tghQZ max < tglQX min, both for a given device and from device to device.
- 5. Transition is measured 200 mV from steady-state voltage with load of Figure 1b.
- 6. This parameter is sampled and not 100% tested.
- 7. Device is continuously selected (E = V_{IL} , \underline{G} = V_{IL}).
- 8. Addresses valid prior to or coincident with E going low.

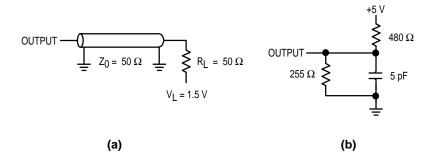


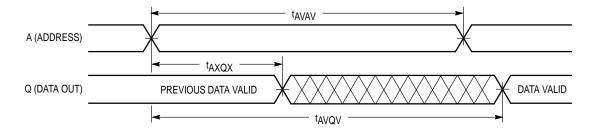
Figure 1. AC Test Loads

TIMING LIMITS

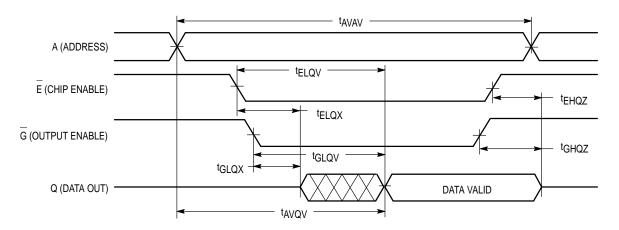
The table of timing values shows either a minimum or a maximum limit for each parameter. Input requirements are specified from the external system point of view. Thus, address setup time is shown as a minimum since the system must supply at least that much time. On the other hand, responses from the memory are specified from the device point of view. Thus, the access time is shown as a maximum since the device never provides data later than that time.

MOTOROLA FAST SRAM MCM6706CR

READ CYCLE 1 (See Note 7)



READ CYCLE 2 (See Note 8)



MCM6706CR MOTOROLA FAST SRAM

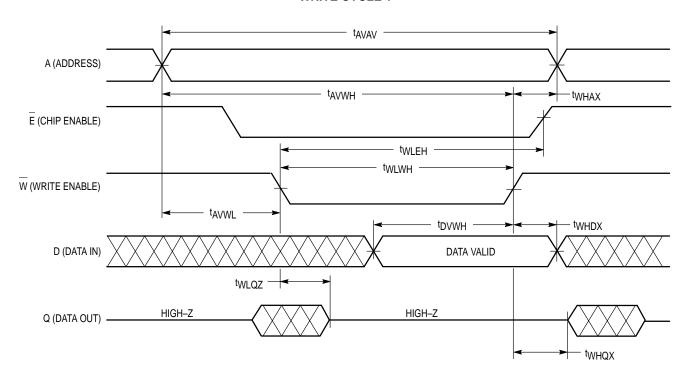
WRITE CYCLE 1 (W Controlled, See Notes 1 and 2)

		MCM6706CR-5		MCM6706CR-5.5			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Write Cycle Time	t _{AVAV}	5	_	5.5	_	ns	3
Address Setup Time	tAVWL	0	_	0	_	ns	
Address Valid to End of Write	^t AVWH	6	_	6	_	ns	
Write Pulse Width	tWLWH, tWLEH	6	_	6	_	ns	
Data Valid to End of Write	^t DVWH	3.5	_	3	_	ns	
Data Hold Time	tWHDX	0	_	0	_	ns	
Write Low to Data High–Z	tWLQZ	_	3.5	_	3.5	ns	4, 5, 6
Write High to Output Active	tWHQX	3	_	3	_	ns	4, 5, 6
Write Recovery Time	tWHAX	0	_	0	_	ns	

NOTES:

- 1. A write occurs during the overlap of E low and W low.
- 2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
- 3. All write cycle timings are referenced from the last valid address to the first transitioning address.
- 4. Transition is measured 200 mV from steady-state voltage with load of Figure 1b.
- 5. Parameter is sampled and not 100% tested.
- 6. At any given voltage and temperature, t_{WLQZ} max is $< t_{WHQX}$ min both for a given device and from device to device.

WRITE CYCLE 1



MOTOROLA FAST SRAM MCM6706CR

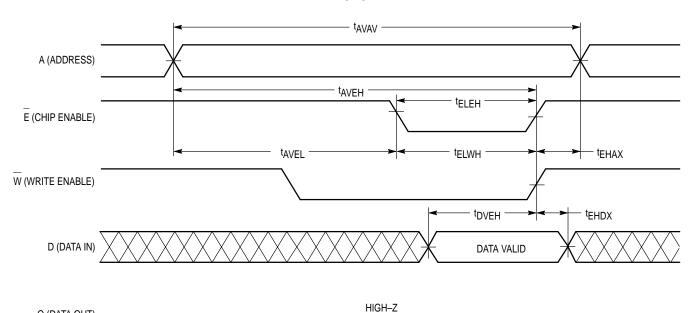
WRITE CYCLE 2 (E Controlled, See Notes 1 and 2)

		MCM6706CR-5		MCM6706CR-5.5			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Write Cycle Time	t _{AVAV}	5	_	5.5	_	ns	3
Address Setup Time	^t AVEL	0	_	0	_	ns	
Address Valid to End of Write	^t AVEH	5	_	5.5	_	ns	
Chip Enable to End of Write	tELWH, tELEH	5	_	5.5	_	ns	4,5
Data Valid to End of Write	^t DVEH	3	_	3	_	ns	
Data Hold Time	tEHDX	0	_	0	_	ns	
Write Recovery Time	^t EHAX	0	_	0	_	ns	

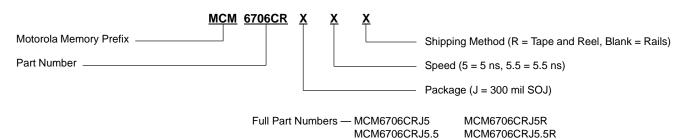
NOTES:

- 1. A write occurs during the overlap of E low and W low.
- 2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
- 3. All_write cycle timing is referenced from the last valid address to the first transitioning address.
- 4. If E goes low coincident with or after W goes low, the output will remain in a high impedance condition.
- 5. If E goes high coincident with or before W goes high, the output will remain in a high impedance condition.

WRITE CYCLE 2



ORDERING INFORMATION (Order by Full Part Number)

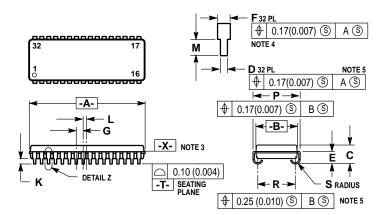


MCM6706CR MOTOROLA FAST SRAM

Q (DATA OUT) -

PACKAGE DIMENSIONS

32-LEAD 300 MIL SOJ CASE 857-02



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DATUM PLANE -X- LOCATED AT TOP OF MOLD PARTING LINE AND COINCIDENT WITH TOP OF LEAD, WHERE LEAD EXITS BODY.
 4. TO BE DETERMINED AT PLANE -X-.
 5. TO BE DETERMINED AT PLANE -T-.
 6. DIMENSION A & B DO NOT INCLUDE MOLD PROTRUSION. MOLD PROTRUSION SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 7. 857-01 IS OBSOLETE, NEW STANDARD 857-02.

	MILLIM	ETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	20.83	21.08	0.820	0.830	
В	7.50	7.74	0.295	0.305	
С	3.26	3.75	0.128	0.148	
D	0.41	0.50	0.016	0.020	
E	2.24	2.48	0.088	0.098	
F	0.67	0.81	0.026	0.032	
G	1.27	BSC	0.050 BSC		
K	0.89	1.14	0.035	0.045	
L	0.64	BSC	0.02	BSC	
N	0.76	1.14	0.030	0.045	
Р	8.38	8.64	0.330	0.340	
R	6.60	6.86	0.260	0.270	
S	0.77	1.01	0.030	0.040	

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